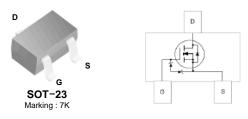
August 2009



2N7002K N-Channel Enhancement Mode Field Effect Transistor

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Pb Free/RoHS Compliant
- ESD HBM=2000V (Typical:3000V) as per JESD22 A114 and ESD CDM=2000V as per JESD22 C101



Absolute Maximum Ratings * T_A = 25°C unless otherwise noted

Symbol	Parameter		Value	Units	
V _{DSS}	Drain-Source Voltage		60	V	
V _{DGR}	Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		60	V	
V _{GSS}	Gate-Source Voltage		±20	V	
Ι _D	Drain Current	Continuous Pulsed	115 800	mA	
ТJ	Operating Junction Temperature Range		-55 to +150	°C	
T _{STG}	Storage Temperature Range		-55 to +150	°C	

* These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

Thermal Characteristics

Symbol	Parameter	Value	Units
PD	Total Device Dissipation Derating above T _A = 25°C	350 2.8	m₩ m₩/°C
R_{\thetaJA}	Thermal Resistance, Junction to Ambient *	350	°C/W

* Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size

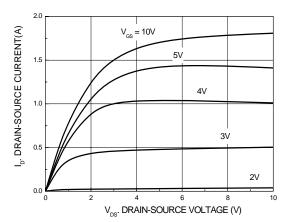
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Symbol	Parameter	Test Condition	MIN	MAX	Units
Off Char	acteristics (Note1)				
BV_{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D =10uA	60		V
I _{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 60V, V_{GS} = 0V V_{DS} = 60V, V_{GS} = 0V, $@T_{C}$ = 125°C		1.0 500	μΑ
I _{GSS}	Gate-Body Leakage	V_{GS} = ±20V, V_{DS} = 0V		±10	μA
On Char	acteristics (Note1)				
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \text{uA}$	1.0	2.5	V
R _{DS(ON)}	Satic Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 0.5A$ $V_{GS} = 4.5V, I_D = 200mA$		2 4	Ω
I _{D(ON)}	On-State Drain Current	$V_{GS} = 10V, V_{DS} = 7.5V$ $V_{GS} = 4.5V, V_{DS} = 10V$	1.5 1.2		А
9 _{FS}	Forward Transconductance	$V_{DS} = 10V, I_{D} = 0.2A$	200		mS
Dynamic	Characteristics				
C _{iss}	Input Capacitance			50	pF
C _{oss}	Output Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz		15	pF
C _{rss}	Reverse Transfer Capacitance			6	pF
Switchin	ng Characteristics				
t _{D(ON)}	Turn-On Delay Time	V _{DD} = 30V, I _{DSS} = 200mA,		5	
t _{D(OFF)}	Turn-Off Delay Time	R _G = 10Ω, V _{GS} = 10V		30	ns

Note1 : Short duration test pulse used to minimize self-heating effect.

Typical Performance Characteristics







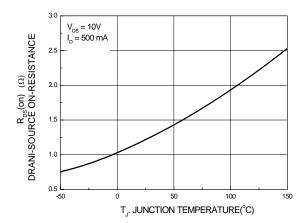


Figure 5. Transfer Characteristics

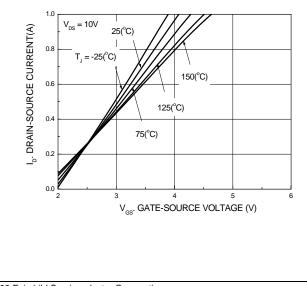
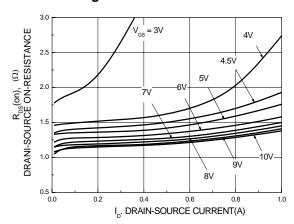


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current





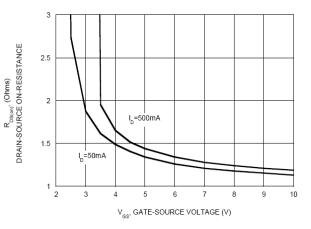
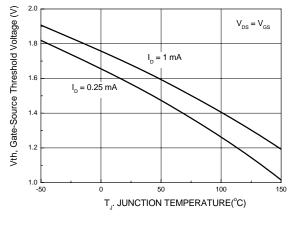
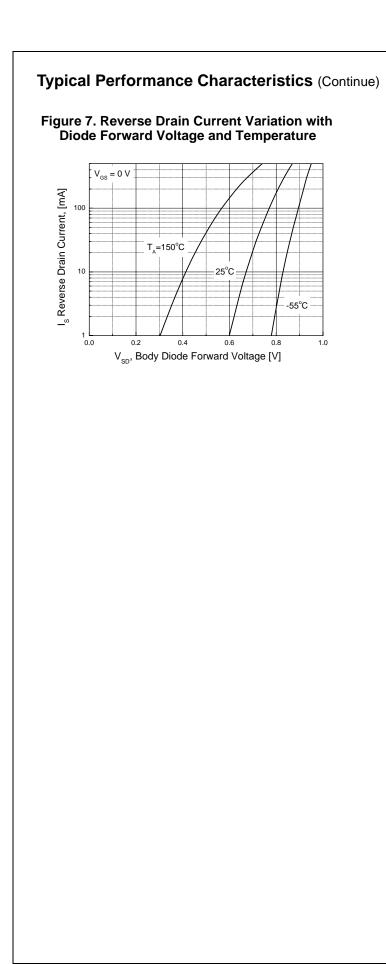
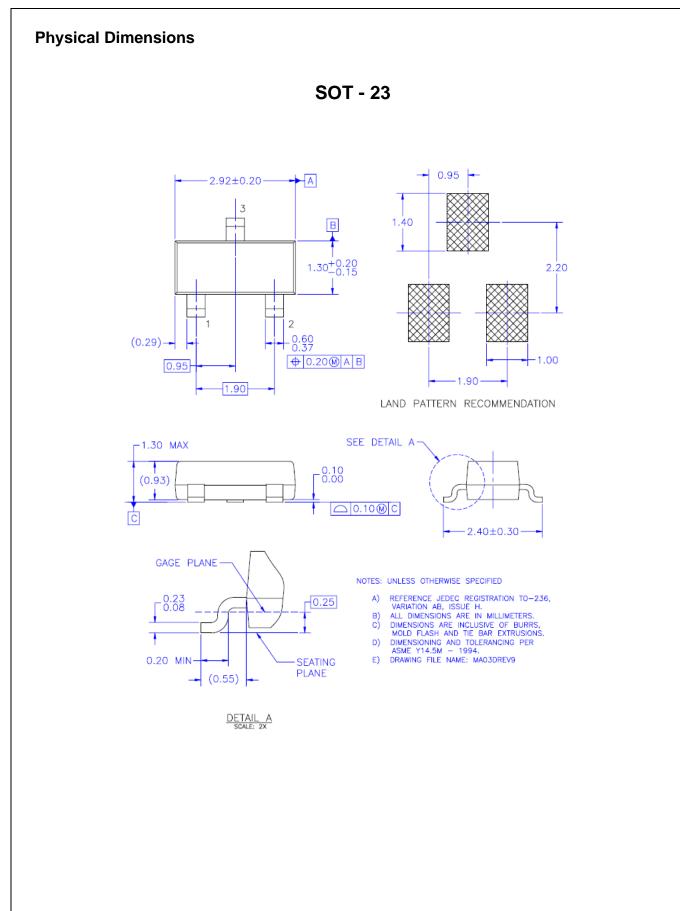


Figure 6. Gate Threshold Variation with Temperature



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